

METHOD OF FORMING WIRING IN SEMICONDUCTOR DEVICES

ABSTRACT OF THE DISCLOSURE

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The invention relates to a method of forming wiring in a semiconductor device. In order to prevent a lift or a crack generated when nitride films having different physical properties come in contact, the invention uses a nitride film having a similar stress characteristic; a nitride film
10 that can be deposited by a low pressure chemical vapor deposition (LPCVD) method in a single type chamber capable of processing wafers one by one, and a nitride film that can be deposited by a low pressure chemical vapor deposition (LPCVD) method in a batch type chamber capable of processing several sheet of wafers.